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April 1st, 2010 Renesas Electronics Corporation

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Wide Temperature Range Version 8 M SRAM (512-kword × 16-bit)



ADE-203-1303B (Z) Rev. 1.0 Oct. 23, 2002

Description

The Hitachi HM6216514I Series is 8-Mbit static RAM organized 524,288-word \times 16-bit. HM6216514I Series has realized higher density, higher performance and low power consumption by employing CMOS process technology (6-transistor memory cell). It offers low power standby power dissipation; therefore, it is suitable for battery backup systems. It is packaged in standard 44-pin plastic TSOPII.

Features

Single 5.0 V supply: 5.0V ± 10 %
Fast access time: 55 ns (Max)

• Power dissipation:

— Active: 10 mW/MHz (Typ)— Standby: 7.5 μW (Typ)

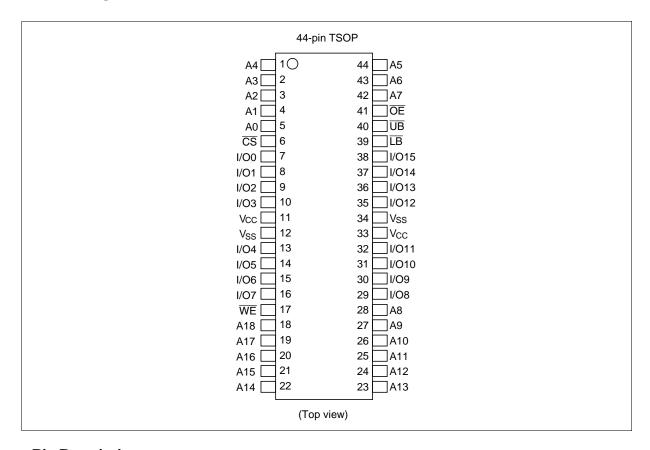
• Completely static memory.

- No clock or timing strobe required
- Equal access and cycle times
- Common data input and output.
 - Three state output
- Battery backup operation.
- Temperature range: -40 to +85°C

Ordering Information

Type No.	Access time	Package
HM6216514LTTI-5SL	55 ns	400-mil 44-pin plastic TSOPII (normal-bend type) (TTP-44DE)

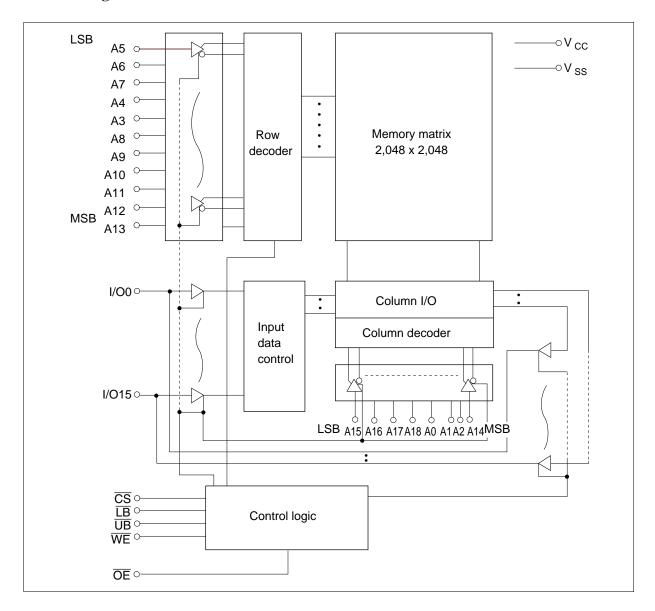
Pin Arrangement



Pin Description

Pin name	Function
A0 to A18	Address input
I/O0 to I/O15	Data input/output
CS	Chip select
WE	Write enable
ŌĒ	Output enable
LB	Lower byte select
ŪB	Upper byte select
V _{cc}	Power supply
V _{ss}	Ground

Block Diagram



Operation Table

CS	WE	OE	UB	LB	I/O0 to I/O7	I/O8 to I/O15	Operation
Н	×	×	×	×	High-Z	High-Z	Standby
×	×	×	Н	Н	High-Z	High-Z	Standby
L	Н	L	L	L	Dout	Dout	Read
L	Н	L	Н	L	Dout	High-Z	Lower byte read
L	Н	L	L	Н	High-Z	Dout	Upper byte read
L	L	×	L	L	Din	Din	Write
L	L	×	Н	L	Din	High-Z	Lower byte write
L	L	×	L	Н	High-Z	Din	Upper byte write
L	Н	Н	×	×	High-Z	High-Z	Output disable

Note: H: V_{IH} , L: V_{IL} , \times : V_{IH} or V_{IL}

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Power supply voltage relative to V _{SS}	V _{cc}	-0.5 to + 7.0	V
Terminal voltage on any pin relative to V _{ss}	V _T	-0.5^{*1} to $V_{CC} + 0.3^{*2}$	V
Power dissipation	P _T	1.0	W
Storage temperature range	Tstg	-55 to +125	°C
Storage temperature range under bias	Tbias	-40 to +85	°C

Notes: 1. V_T min: -3.0 V for pulse half-width ≤ 30 ns.

2. Maximum voltage is +7.0 V.

DC Operating Conditions

Parameter	Symbol	Min	Тур	Max	Unit	Note
Supply voltage	V _{cc}	4.5	5.0	5.5	V	
	V _{ss}	0	0	0	V	
Input high voltage	V_{IH}	2.2	_	V _{cc} + 0.	3 V	
Input low voltage	V_{IL}	-0.3	_	0.8	V	1
Ambient temperature range	Ta	-40	_	85	°C	

Note: 1. V_{IL} min: -3.0 V for pulse half-width ≤ 30 ns.

DC Characteristics

Parameter	Symbol	Min	Typ*1	Max	Unit	Test conditions
Input leakage current	I _{LI}	_	_	1	μΑ	$Vin = V_{SS}$ to V_{CC}
Output leakage current	I _{LO}	_	_	1	μΑ	
Operating current	I _{cc}	_	_	20	mA	$\overline{\text{CS}} = \text{V}_{\text{IL}}$, Others = $\text{V}_{\text{IH}}/\text{V}_{\text{IL}}$, $\text{I}_{\text{I/O}} = 0 \text{ mA}$
Average operating current	I _{CC1}	_	16	35	mA	Min. cycle, duty = 100%, $I_{I/O} = 0$ mA, $\overline{CS} = V_{IL}$, Others = V_{IH}/V_{IL}
	I _{CC2}	_	2	5	mA	$\begin{split} &\text{Cycle time} = 1 \mu\text{s}, \text{duty} = 100\%, \\ &\text{I}_{\text{I/O}} = 0 \text{mA}, \overline{\text{CS}} \leq 0.2 \text{V}, \\ &\text{V}_{\text{IH}} \geq \text{V}_{\text{CC}} - 0.2 \text{V}, \text{V}_{\text{IL}} \leq 0.2 \text{V} \end{split}$
Standby current	I _{SB}	_	0.1	0.3	mA	$\overline{\text{CS}} = V_{\text{IH}}$
Standby current	I _{SB1}	_	0.8	10	μΑ	0 V \leq Vin (1) $\overline{CS} \geq V_{CC} - 0.2 \text{ V or}$ (2) $\overline{LB} = \overline{UB} \geq V_{CC} - 0.2 \text{ V},$ $\overline{CS} \leq 0.2 \text{ V}$
Output high voltage	V _{OH}	2.4	_	_	V	$I_{OH} = -1 \text{ mA}$
Output low voltage	V _{OL}	_	_	0.4	V	I _{OL} = 2.1 mA

Notes: 1. Typical values are at $V_{cc} = 5.0 \text{ V}$, $Ta = +25^{\circ}\text{C}$ and not guaranteed.

Capacitance (Ta = +25°C, f = 1.0 MHz)

Parameter	Symbol	Min	Тур	Max	Unit	Test conditions	Note
Input capacitance	Cin	_	_	8	pF	Vin = 0 V	1
Input/output capacitance	$C_{I/O}$	_	_	10	pF	$V_{I/O} = 0 V$	1

Note: 1. This parameter is sampled and not 100% tested.

AC Characteristics (Ta = -40 to +85 °C, $V_{\rm CC}$ = 5.0 V \pm 10 %, unless otherwise noted.)

Test Conditions

• Input pulse levels: $V_{IL} = 0.4 \text{ V}$, $V_{IH} = 2.2 \text{ V}$

• Input rise and fall time: 5 ns

• Input and output timing reference levels: 1.5 V

• Output load: $1 \text{ TTL Gate} + C_L (50 \text{ pF}) (Including scope and jig)$

Read Cycle

		HM621	6514I		
		-5			
Parameter	Symbol	Min	Max	Unit	Notes
Read cycle time	t _{RC}	55	_	ns	
Address access time	t _{AA}	_	55	ns	
Chip select access time	t _{ACS}	_	55	ns	
Output enable to output valid	t _{OE}	_	35	ns	
Output hold from address change	t _{oh}	10	_	ns	
LB, UB access time	t _{BA}	_	55	ns	
Chip select to output in low-Z	t _{CLZ}	10	_	ns	2, 3
LB, UB enable to low-z	t _{BLZ}	5	_	ns	2, 3
Output enable to output in low-Z	t _{OLZ}	5	_	ns	2, 3
Chip deselect to output in high-Z	t _{CHZ}	0	20	ns	1, 2, 3
LB, UB disable to high-Z	t _{BHZ}	0	20	ns	1, 2, 3
Output disable to output in high-Z	t _{OHZ}	0	20	ns	1, 2, 3

Write Cycle

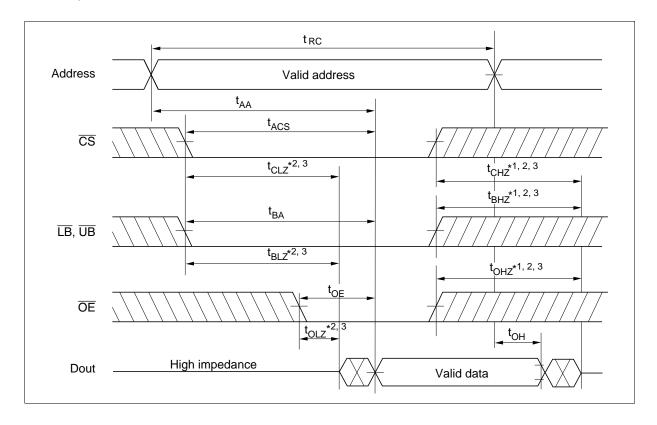
		-5			
Parameter	Symbol	Min Max		Unit	Notes
Write cycle time	t _{wc}	55	_	ns	
Address valid to end of write	t _{AW}	50	_	ns	
Chip selection to end of write	t _{cw}	50	_	ns	5
Write pulse width	t _{WP}	40	_	ns	4
LB, UB valid to end of write	t _{BW}	50	_	ns	
Address setup time	t _{AS}	0	_	ns	6
Write recovery time	t _{wR}	0	_	ns	7
Data to write time overlap	t _{DW}	25	_	ns	
Data hold from write time	t _{DH}	0	_	ns	
Output active from end of write	t _{ow}	5	_	ns	2
Output disable to output in high-Z	t _{OHZ}	0	20	ns	1, 2
Write to output in high-Z	t _{whz}	0	20	ns	1, 2

Notes: 1. t_{CHZ} , t_{OHZ} , t_{WHZ} and t_{BHZ} are defined as the time at which the outputs achieve the open circuit conditions and are not referred to output voltage levels.

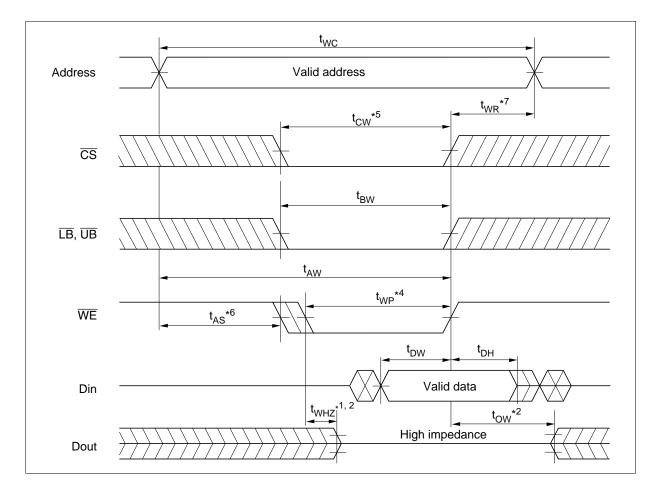
- 2. This parameter is sampled and not 100% tested.
- 3. At any given temperature and voltage condition, t_{HZ} max is less than t_{LZ} min both for a given device and from device to device.
- 4. A write occures during the overlap of a low \overline{CS} , a low \overline{WE} and a low \overline{LB} or a low \overline{UB} . A write begins at the latest transition among \overline{CS} going low, \overline{WE} going low and \overline{LB} going low or \overline{UB} going low. A write ends at the earliest transition among \overline{CS} going high, \overline{WE} going high and \overline{LB} going high or \overline{UB} going high. t_{WP} is measured from the beginning of write to the end of write.
- 5. t_{cw} is measured from the later of \overline{CS} going low to the end of write.
- 6. $t_{\rm AS}$ is measured from the address valid to the beginning of write.
- 7. t_{wR} is measured from the earliest of \overline{CS} or \overline{WE} going high to the end of write cycle.

Timing Waveform

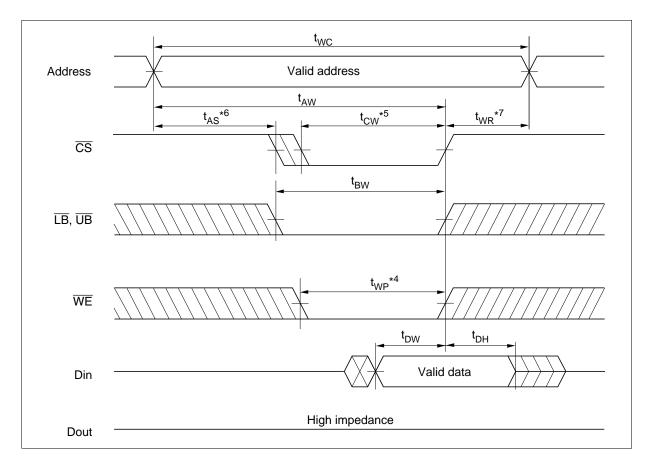
Read Cycle



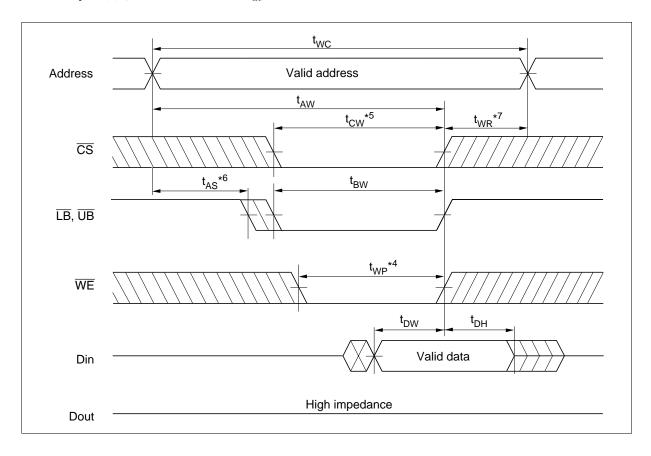
Write Cycle (1) ($\overline{\text{WE}}$ Clock)



Write Cycle (2) ($\overline{\text{CS}}$ Clock, $\overline{\text{OE}} = V_{\text{IH}}$)



Write Cycle (3) (\overline{LB} , \overline{UB} Clock, \overline{OE} = V_{IH})



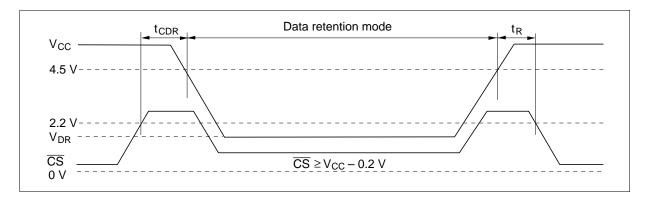
Low V_{CC} **Data Retention Characteristics** ($Ta = -40 \text{ to } +85^{\circ}\text{C}$)

Parameter	Symbol	Min	Typ*2	Max	Unit	Test conditions*1
V _{cc} for data retention	V_{DR}	2.0	_	_	V	$\begin{array}{c} \text{Vin} \geq 0\text{V} \\ \text{(1)} \ \overline{\text{CS}} \geq \text{V}_{\text{CC}} - 0.2 \text{ V or} \\ \text{(2)} \ \overline{\text{LB}} = \overline{\text{UB}} \geq \text{V}_{\text{CC}} - 0.2 \text{ V} \\ \overline{\text{CS}} \leq 0.2 \text{ V} \end{array}$
Data retention current	I _{CCDR}	_	0.8	10	μΑ	$V_{CC} = 3.0 \text{ V}, \text{ Vin } \ge 0\text{V}$ (1) $\overline{CS} \ge V_{CC} - 0.2 \text{ V}$ or (2) $\overline{LB} = \overline{UB} \ge V_{CC} - 0.2 \text{ V}$ $\overline{CS} \le 0.2 \text{ V}$
Chip deselect to data retention time	t _{CDR}	0	_	_	ns	See retention waveform
Operation recovery time	t _R	t _{RC} *3	_	_	ns	_

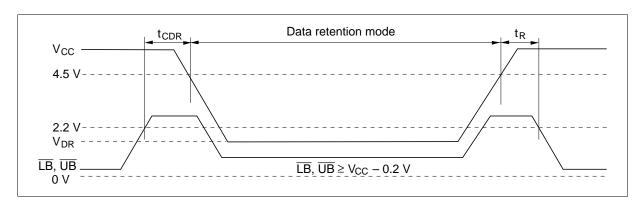
Notes: 1. $\overline{\text{CS}}$ controls address buffer, $\overline{\text{WE}}$ buffer, $\overline{\text{OE}}$ buffer, $\overline{\text{LB}}$, $\overline{\text{UB}}$ buffer and Din buffer. If $\overline{\text{CS}}$ controls data retention mode, Vin levels (address, $\overline{\text{WE}}$, $\overline{\text{OE}}$, $\overline{\text{LB}}$, $\overline{\text{UB}}$, $\overline{\text{I/O}}$) can be in the high impedance state. If $\overline{\text{LB}}$, $\overline{\text{UB}}$ controls data retention mode, $\overline{\text{LB}}$, $\overline{\text{UB}}$ must be $\overline{\text{LB}}$ = $\overline{\text{UB}}$ \geq V_{CC} - 0.2 V, $\overline{\text{CS}}$ must be $\overline{\text{CS}}$ \leq 0.2 V. The other input levels (address, $\overline{\text{WE}}$, $\overline{\text{OE}}$, $\overline{\text{I/O}}$) can be in the high impedance state.

- 2. Typical values are at V_{CC} = 3.0 V, Ta = +25°C and not guaranteed.
- 3. t_{RC} = read cycle time.

Low V_{CC} Data Retention Timing Waveform (1) $(\overline{\text{CS}} \text{ Controlled})$

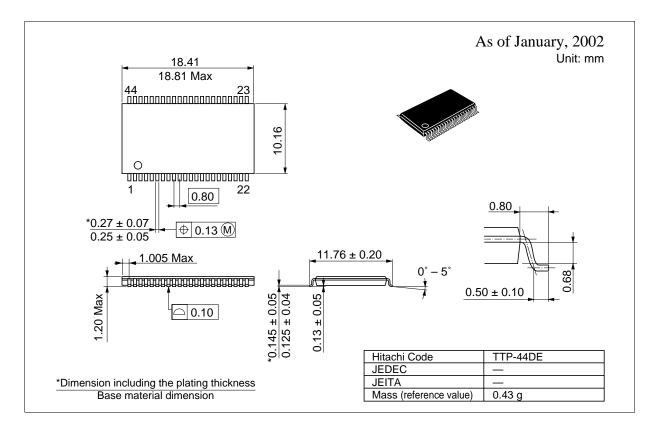


Low V_{CC} Data Retention Timing Waveform (2) $(\overline{LB},\overline{UB}$ Controlled)



Package Dimensions

HM6216514LTTI Series (TTP-44DE)



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